

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

Sheet 1 of 1

ATTY. DOCKET NO.

SERIAL NO.

M-300 US

06/843,454

APPLICANT

Richard A. Blanchard

FILING DATE

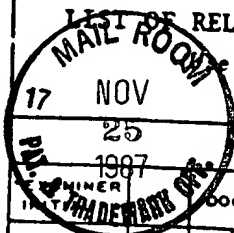
03/24/86

GROUP

114

LIST OF RELEVANT ART CITED BY APPLICANT

(Indicate several sheets if necessary)



U.S. PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
570	AA	3 3 9 8 3 3 9	8/16/83	Blanchard et al.	29	571	9/9/81
570	AB	4 6 3 9 7 5 4	1/27/87	Wheatley, Jr. et al.	357	23.4	2/25/85
570	AC	4 6 8 2 4 0 5	7/28/87	Blanchard et al.	29	571	7/22/85
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
570	AL	53 1 4 9 7 7 1	12/27/78	Japan (Matsushita Elec.)	357	23.4	X
570	AM	55 1 4 6 9 7 6	11/15/80	Japan (Hideshima)			X
	AN						
	AO						
	AP						

OTHER

ART (Including Author, Title, Date, Pertinent Pages, Etc.)

570	AR	Baliga et al. "THE INSULATED GATE TRANSISTOR: A NEW THREE-TERMINAL MOS-CONTROLLED BIPOLAR POWER DEVICE", IEEE Transactions on Electron Devices, Vol. ED-31, No. 6, June 1984, pgs. 821-828.
570	AS	Ueda et al. "A NEW VERTICAL POWER MOSFET STRUCTURE WITH EXTREMELY REDUCED ON-RESISTANCE", IEEE Transactions on Electron Devices, Vol. ED-32, No. 1, January 1985, pgs. 2-6
570	AT	Rung et al. "DEEP TRENCH ISOLATED CMOS DEVICES", IEDM 1982, pgs. 237-240.

EXAMINER

D. T. Ozaki

DATE CONSIDERED

12-11-87

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.